



Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, CA 90638
Phone: (562) 404-4474 * Fax: (562) 404-1773
ssdi@ssdi-power.com * www.ssdi-power.com

1N8021 thru 1N8023 SERIES

1 AMP
100 – 200 VOLTS
5 nsec
HYPER FAST
RECOVERY RECTIFIER

Designer's Data Sheet

Part Number/Ordering Information ^{1/}

1N802 _ _ _

- L **Screening** ^{2/}
 - _ = Not Screened
 - TX = TX Level
 - TXV = TXV Level
 - S = S Level
- L **Package Type**
 - _ = Axial Leaded
 - SMS = Surface Mount Square Tab
- L **Device Type** (VRWM)
 - 1 = 100 V
 - 2 = 150 V
 - 3 = 200 V

FEATURES:

- Hyper fast reverse recovery time: 5 ns Max
- Low forward voltage drop
- Low reverse leakage current
- Avalanche breakdown
- Void free ceramic frit glass construction
- High temperature category I eutectic metallurgical bond
- Hermetically sealed
- Solid silver leads
- Excellent liquid-to-liquid cryogenic thermal shock performance
- Available in axial & square tab versions
- For high efficiency applications
- TX, TXV, and S-Level screening available^{2/}
- Available as a QPL product per MIL-PRF-19500/770
- Replacement for 1N6638, 1N6642 and 1N5806

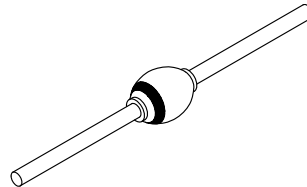
MAXIMUM RATINGS ^{3/}

RATING		SYMBOL	VALUE	UNIT
Peak Repetitive Reverse Voltage DC Blocking Voltage	1N8021	V_{RWM}	100	Volts
	1N8022	V_R	150	
	1N8023		200	
Average Rectified Forward Current (Resistive load, 60 Hz, sine wave, $T_C = 25^\circ C$)		I_o	1	Amp
Peak Surge Current (8.3 msec pulse, half sine wave superimposed on I_o , allow junction to reach equilibrium between pulses, $T_C = 25^\circ C$)		I_{FSM}	20	Amps
Operating & Storage Temperature		T_{OP} and T_{STG}	-65 to +175	$^\circ C$
Thermal Resistance SMS- Junction to End Tab Axial- Junction to Lead @ .375"		$R_{\theta JE}$	20	$^\circ C/W$
		$R_{\theta JL}$	80	

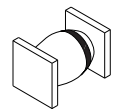
NOTES:

- 1/ For ordering information, price, and availability - contact factory.
- 2/ Screening based on MIL-PRF-19500. Screening flows available on request.
- 3/ Unless otherwise specified, all electrical characteristics @25°C.

Axial Leaded



SMS



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

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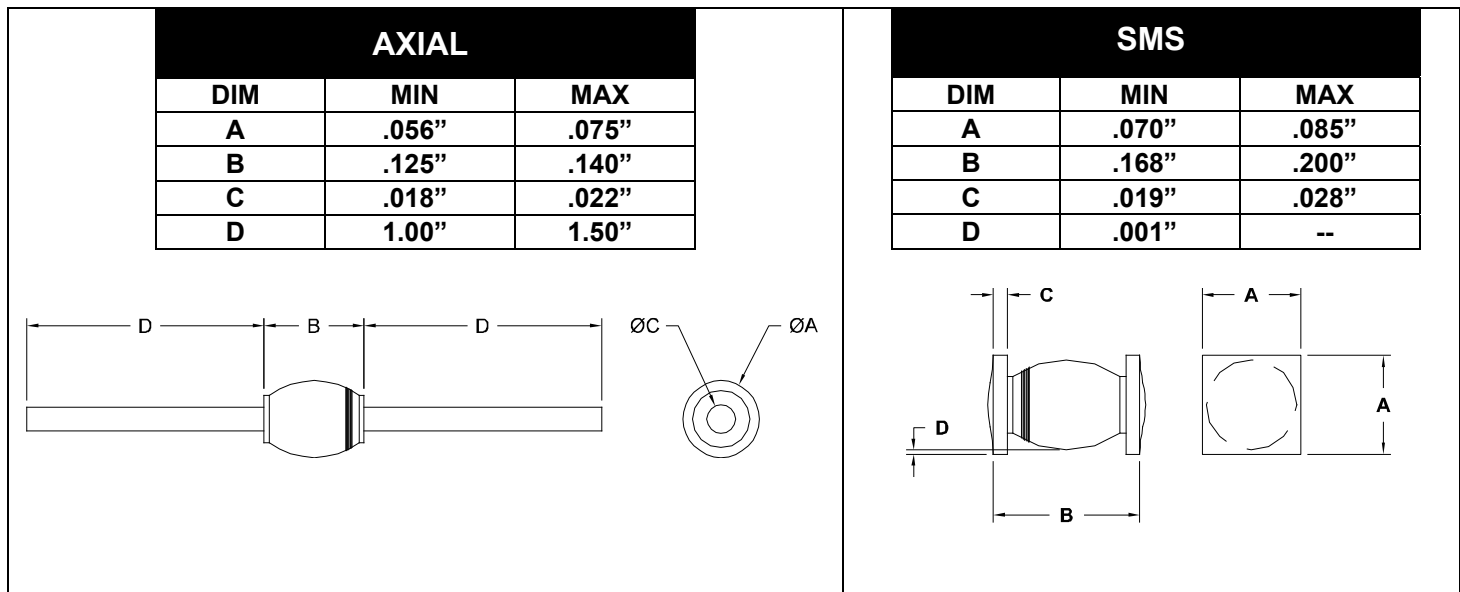
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 SERIES**

ELECTRICAL CHARACTERISTICS ^{3/}

CHARACTERISTICS	SYMBOL	LIMIT	UNIT
Maximum Instantaneous Forward Voltage Drop (Pulsed, T _A = 25°C)	@ I _F = 1mA	V _{F1}	0.525
	@ I _F = 10mA	V _{F2}	0.650
	@ I _F = 100mA	V _{F3}	0.800
	@ I _F = 200mA	V _{F4}	0.850
	@ I _F = 500mA	V _{F5}	0.910
	@ I _F = 1A	V _{F6}	0.980
Maximum Instantaneous Forward Voltage Drop (Pulsed, T _A = 150°C)	@ I _F = 10mA	V _{F7}	0.500
	@ I _F = 100mA	V _{F8}	0.620
Maximum Instantaneous Forward Voltage Drop (Pulsed, T _A = -55°C)	@ I _F = 10mA	V _{F9}	0.810
	@ I _F = 100mA	V _{F10}	0.900
Minimum Breakdown Voltage I _R = 100 μA	1N8021	BV _R	110
	1N8022		165
	1N8023		220
Maximum Reverse Leakage Current (300 μs Pulse Minimum , T _A = 25°C)	@ V _R = 20V	I _{R1}	80
	@ V _R = 75V	I _{R2}	120
	@ V _R = max rated	I _{R3}	750
Maximum Reverse Leakage Current (300 μs Pulse Minimum , T _A = 125°C)	@ V _R = 20V	I _{R4}	50
	@ V _R = 75V	I _{R5}	75
	@ V _R = max rated	I _{R6}	150
Maximum Junction Capacitance (T _A = 25°C , f = 1MHz) V _R = 0V	C _{J1}	6	pf
Maximum Junction Capacitance (T _A = 25°C , f = 1MHz) V _R = 1.5V	C _{J2}	5	pf
Maximum Junction Capacitance (T _A = 25°C , f = 1MHz) V _R = 10V	C _{J3}	4	pf
Maximum Reverse Recovery Time (I _F = 50 mA, I _R = 100 mA, I _{RR} = 25 mA)	t _{rr}	5	nsec
Maximum Forward Recovery Time (I _F = 50 mA)	t _{fr}	20	nsec



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